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IN THE CLAIMS:

1. (Currently Amended) A semiconductor manufacturing apparatus comprising:

~~means for transferring an object to be processed;~~

~~at least one plasma generating means for performing a plasma treatment; and  
means for moving the plasma generating means in the intersecting direction with a  
transferring direction of the object to be processed~~

at least two chambers for processing a first part of an object by a first plasma  
treatment under atmospheric pressure or approximate to atmospheric pressure in a  
first one of the two chambers and for processing a second part of the object by a  
second plasma treatment under atmospheric pressure or approximate to atmospheric  
pressure in a second one of the two chambers simultaneously with the first plasma  
treatment;

a first plasma generating device for performing the first plasma treatment in  
the first one of the two chambers; and

a second plasma generating device for performing the second plasma  
treatment in the second one of the two chambers.

wherein the object is transferred in the two chambers along a first direction  
and the first plasma generating device and the second plasma generating device are  
moved along a second direction intersecting with the first direction.

2. (Canceled)

3. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein ~~the means for transferring the object to be processed transfers the  
object to be processed unidirectionally~~ the first direction is a unidirection.

4. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the object is transferred continuously or with the use of step-feed ~~by the means for transferring the object to be processed.~~

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5. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment, wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed, and wherein film formation treatment, etching treatment or ashing treatment is performed on the object to be processed by transferring of the object to be processed and generating plasma in at least one of the plurality of plasma generating means.

6. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the plasma generating means has a structure which is performed under atmospheric pressure or approximate to atmospheric pressure.

7. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

8. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

9. (Currently Amended) A semiconductor manufacturing apparatus comprising:

~~means for transferring an object to be processed;~~

~~at least one droplet spraying means for spraying a droplet to the object to be processed; and~~

~~means for moving the droplet spraying means in the intersecting direction with a transferring direction of the object to be processed~~

at least two chambers for processing a first part of an object by a first plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a

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first one of the two chambers and for processing a second part of the object by a second plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a second one of the two chambers simultaneously with the first plasma treatment;

a first plasma generating device for performing the first plasma treatment in the first one of the two chambers;

a second plasma generating device for performing the second plasma treatment in the second one of the two chambers; and

an ink-jet device for applying a droplet to the object.

wherein the object is transferred in the two chambers along a first direction and the ink-jet device is moved along a second direction intersecting with the first direction.

10. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the ~~spraying~~ applying of the droplet is performed to a surface of the object under atmospheric pressure or adjacent approximate to atmospheric pressure.

11. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein ~~the means for transferring the object to be processed transfers the object to be processed unidirectionally~~ the first direction is a unidirection.

12. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the object is transferred continuously or with the use of step-feed ~~by the means for transferring the object.~~

13. (Withdrawn) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is an organic solvent containing organic resin or metal element.

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14. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of droplet spraying means for spraying a droplet onto the surface of the object to be processed, wherein the plurality of droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed, and a droplet is attached to the object to be processed by the transfer of the object to be processed and spraying a droplet from at least one of the plurality of droplet spraying means.

15. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is attached under atmospheric pressure or approximate to atmospheric pressure.

16. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

17. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

18. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is an organic solvent containing organic resin or a metal element.

19. (Currently Amended) A semiconductor manufacturing apparatus comprising:

~~means for transferring an object to be processed;~~

at least one plasma generating means device for processing an object by performing a plasma treatment under atmospheric pressure or approximate to atmospheric pressure; and

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at least one ~~droplet spraying means~~ ink-jet device for ~~spraying~~ applying a droplet to the object ~~to be processed~~;

~~first means for moving the plasma generating means in the intersecting direction with a transferring direction of the object; and~~

~~second means for moving the droplet spraying means in the intersection direction with the transferring direction of the object~~

wherein the object is transferred in a treatment chamber along a first direction and the plasma generating device is moved along a second direction intersecting with the first direction, and

wherein the ink-jet device is moved along a third direction intersecting with the first direction.

20. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating ~~means~~ device for forming a film over the object, etching the object or ashing the object.

21. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein ~~the means for transferring the object to be processed transfers the object to be processed unidirectionally~~ the first direction is a unidirection.

22. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed ~~by the means for transferring the object to be processed.~~

23. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein a plurality of treatments selected from the film forming treatment, the etching treatment, the ashing treatment or the ~~spraying~~ applying of the droplet are performed simultaneously.



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24. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment on the object to be processed, a plurality of droplet spraying means for attaching a droplet on the object to be processed,

wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the plurality of the droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the film formation treatment, the etching treatment or the ashing treatment is performed on the object to be processed by the transfer of the object to be processed and generating plasma in at least one of the plurality of plasma generating means, and

wherein attach the droplet on the object to be processed by the transfer of the object to be processed and spraying the droplet from the droplet spraying means.

25. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the film formation treatment, the etching treatment or the attachment of the droplet is performed under atmospheric pressure or adjacent to atmospheric pressure.

26. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

27. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

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28. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein a plurality of treatment selected from the film formation treatment, the etching treatment, the ashing treatment or the attachment treatment of the droplet are performed simultaneously.

29. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the first plasma treatment is performed by the first plasma generating means device for forming a film over the object, etching the object, or ashing the object.

30. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the first plasma treatment is performed by the first plasma generating means device while transferring the object and moving the first plasma generating means device.

31. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is attached onto a surface of the object ~~to be processed~~ while transferring the object and moving the ~~droplet-spraying means~~ ink-jet device.

32. (Canceled)

33. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating means device while transferring the object and moving the plasma generating means device.

34. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the ~~spraying~~ applying of the droplet is performed to a surface of the object under atmospheric pressure or adjacent approximate to atmospheric pressure.

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35. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein ~~the means for transferring the object to be processed transfers the object to be processed unidirectionally~~ the first direction is a unidirection.

36. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed ~~by the means for transferring the object.~~

37. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is an organic solvent containing resin or metal element.

38. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is attached onto a surface of the object to be processed while transferring the object and moving the ~~droplet spraying means~~ ink-jet device.

39. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9 further comprising ~~a plurality of a~~ third plasma generating ~~means~~ device for performing a third plasma treatment.

40. (Currently Amended) A semiconductor manufacturing apparatus according to claim ~~37~~ 39, wherein the third plasma treatment is performed by the ~~plurality of third~~ plasma generating ~~means~~ device for forming a film over the object, etching the object, or ashing the object.

41. (New) A semiconductor manufacturing apparatus according to claim 1 wherein each of the first plasma generating device and the second plasma generating device comprises a first electrode and a second electrode for generating a plasma



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between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

42. (New) A semiconductor manufacturing apparatus according to claim 9 wherein each of the first plasma generating device and the second plasma generating device comprises a first electrode and a second electrode for generating a plasma between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

43. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the ink-jet device comprises a nozzle provided with a hole for pushing out the droplet from the hole.

44. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the plasma generating device comprises a first electrode and a second electrode for generating a plasma between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

45. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the ink-jet device comprises a nozzle provided with a hole for pushing out the droplet from the hole.